

NTL4502N

Quad Power MOSFET

24 V, 15 A, N-Channel, PinPAK™ Package



ON Semiconductor®

<http://onsemi.com>

Features

- Four N-Channel MOSFETs in a Single Package
- High Drain Current (Up to 80A per Device, Single Pulse $t_p < 10 \mu\text{s}$, $R_{\theta JC} = 1.5 \text{ }^\circ\text{C/W}$)
- High Input Impedance for Ease of Drive
- Ultra Low On-resistance ($R_{DS(on)}$) Provides Low Conduction Losses
- Very Fast Switching Times Provides Low Switching Losses
- Low Parasitic Inductance
- Low Stored Charge for Efficient Switching
- Very Low V_{SD} Ideal for Synchronous Rectification
- 200% Footprint Reduction Compared to Similar DPAK Solution for the Same Power
- Advanced Leadless Power Integrated Package (PinPAK)

Applications

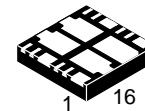
- DC-DC Converters
- Motherboard/Server Voltage Regulator
- Telecomm/Industrial Power Supply
- H-Bridge Circuits
- Low Voltage Motor Control

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

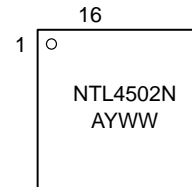
Parameter	Symbol	Value	Units
Drain-to-Source Voltage	V_{DSS}	24	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	Steady State	$T_A=25^\circ\text{C}$	15
		$T_A=85^\circ\text{C}$	10.9
		$t \leq 10 \text{ s}$, $T_A=25^\circ\text{C}$	18.8
Power Dissipation (Note 1)	Steady State	$T_A=25^\circ\text{C}$	2.9
		$t \leq 10 \text{ s}$	4.5
Continuous Drain Current (Note 2)	Steady State	$T_A=25^\circ\text{C}$	11.4
		$T_A=85^\circ\text{C}$	8.2
		$T_A=25^\circ\text{C}$	1.7
Power Dissipation (Note 2)			
Pulsed Drain Current	$t_p=10 \mu\text{s}$	I_{DM}	32
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	15	A
Single Pulse Drain-to-Source Avalanche Energy – ($V_{DD}=25 \text{ V}$, $V_{GS}=10 \text{ V}$, $I_{PK}=60 \text{ A}$, $L=0.1 \text{ mH}$, $R_G=1.0 \text{ k}\Omega$)	EAS	80	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_D MAX (Note 1)
24 V	8.0 m Ω @ 4.5 V	15 A
	11.2 m Ω @ 10 V	

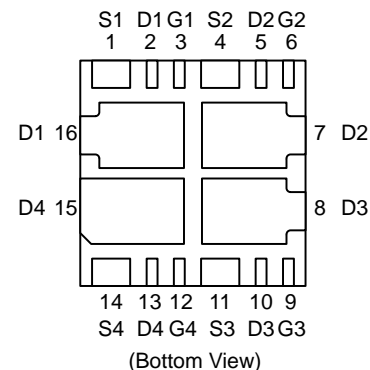
MARKING DIAGRAM



CASE 495
PinPAK
STYLE 1



xx = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week



Pinout Diagram

ORDERING INFORMATION

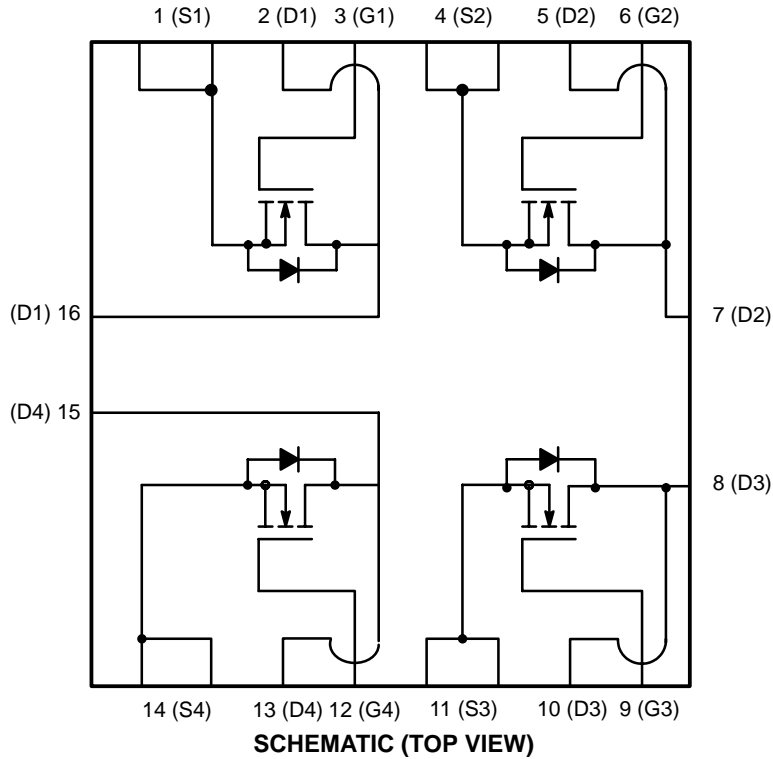
Device	Package	Shipping
NTL4502NT1	PinPAK	1500 / Reel

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Case (Drain)	$R_{\theta JC}$	1.5	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	43	
Junction-to-Ambient – $t \leq 10$ s (Note 1)	$R_{\theta JA}$	27.5	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	75	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface-mounted on FR4 board using minimum recommended pad size (Cu area = 0.440 in sq).



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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	24	27.5		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			25.5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	T _J =25°C		1.5	μA
			T _J =125°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0	1.5	2.0	V
Gate Threshold Voltage Temperature Coefficient	V _{GS(th)} /T _J			-4.1		mV/°C
Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 15 A		11.2	13	mΩ
		V _{GS} = 10 V, I _D = 15 A		8.0	11	
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 15 A		27		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1.0 MHz		1070	1605	pF
Output Capacitance	C _{oss}			408	612	
Reverse Transfer Capacitance	C _{rss}			142	213	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, I _D = 15 A, V _{DS} = 24 V		13		nC
Threshold Gate Charge	Q _{G(TH)}			1.6		
Gate-to-Source Charge	Q _{GS}			3.3		
Gate-to-Drain Charge	Q _{GD}			7.0		

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DD} = 12 V, I _D = 15 A, R _G = 3.0 Ω		5.0	8.5	ns
Rise Time	t _r			28	47	
Turn-Off Delay Time	t _{d(OFF)}			22	37	
Fall Time	t _f			6.0	10	

SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 12 V, I _D = 15 A, R _G = 3.0 Ω		9.5	16	ns
Rise Time	t _r			33	55	
Turn-Off Delay Time	t _{d(OFF)}			14	23.5	
Fall Time	t _f			7.5	12.5	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 15 A	T _J =25°C	0.8	1.2	V
			T _J =125°C	0.7		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, di _S /dt = 100 A/μs, I _S = 15 A		31		ns
Charge Time	t _a			17		
Discharge Time	t _b			14		
Reverse Recovery Charge	Q _{RR}			20		nC

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

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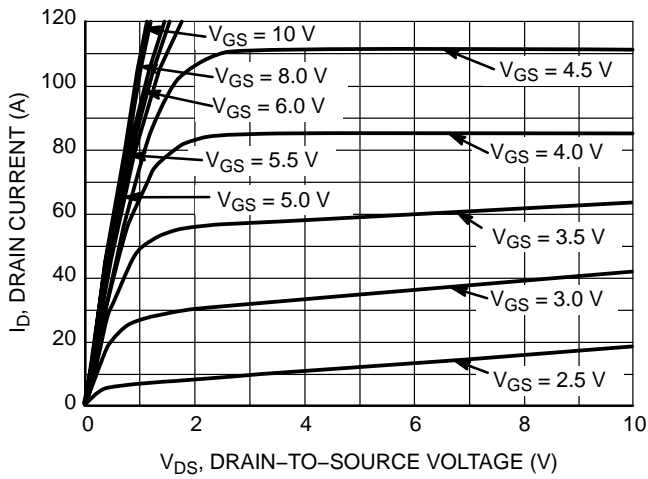


Figure 1. On-Region Characteristics

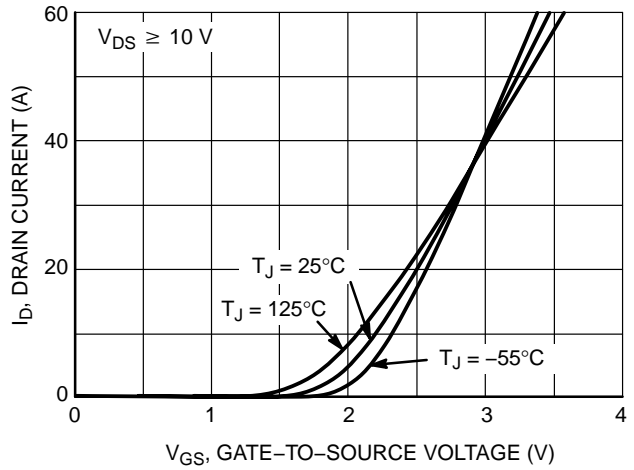


Figure 2. Transfer Characteristics

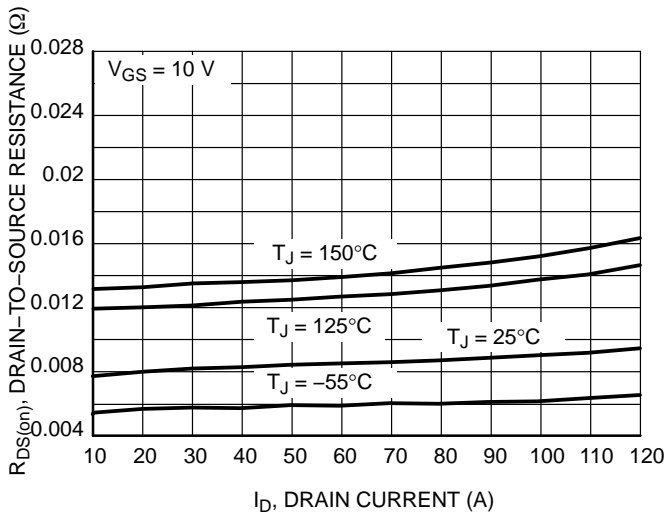


Figure 3. On-Resistance versus Drain Current and Temperature

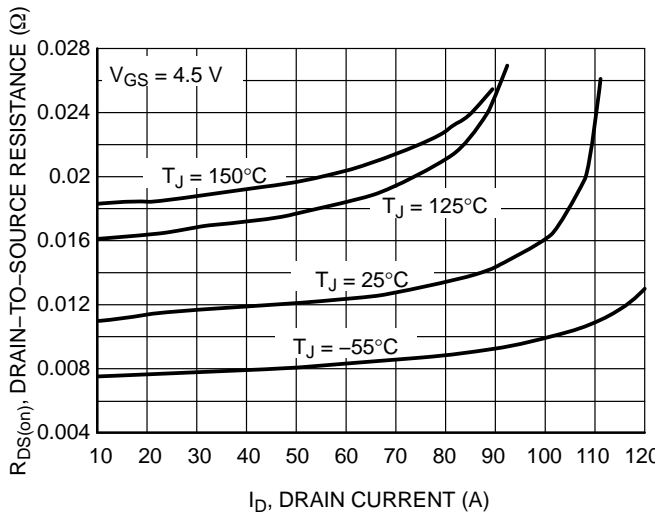


Figure 4. On-Resistance versus Drain Current and Temperature

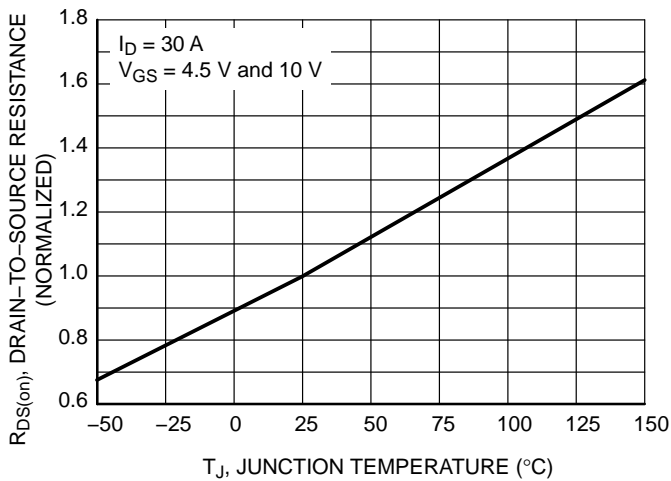


Figure 5. On-Resistance Variation with Temperature

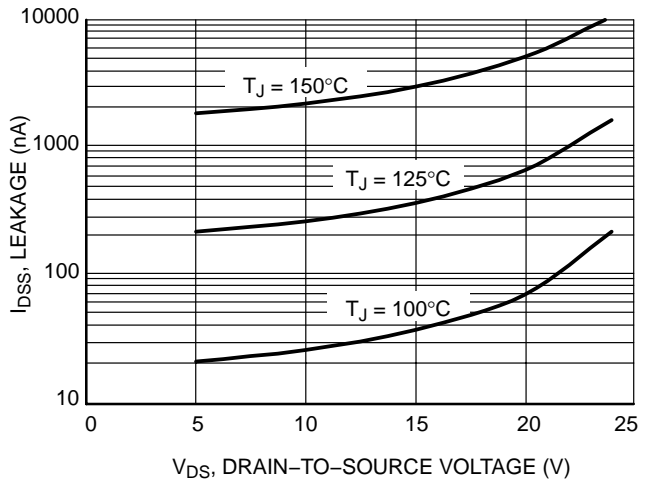


Figure 6. Drain-to-Source Leakage Current versus Voltage

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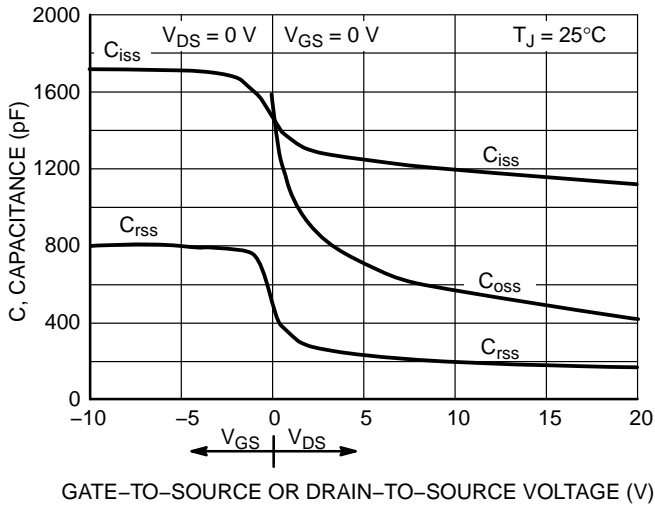


Figure 7. Capacitance Variation

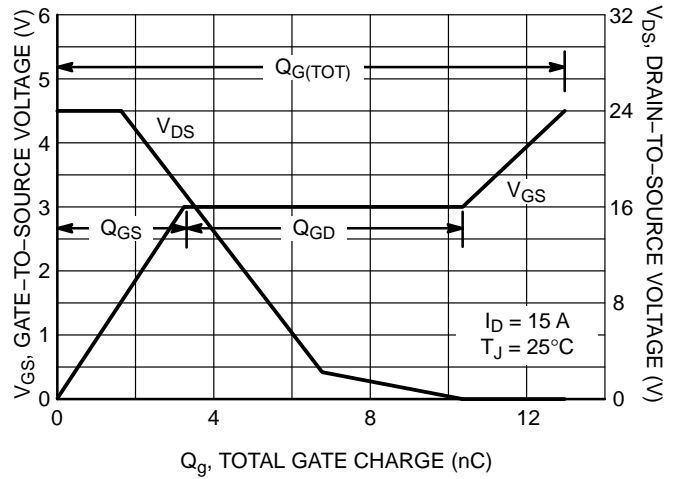


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

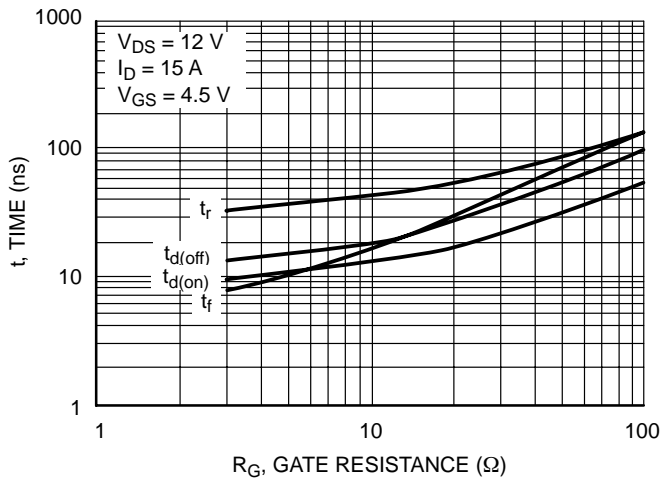


Figure 9. Resistive Switching Time Variation versus Gate Resistance

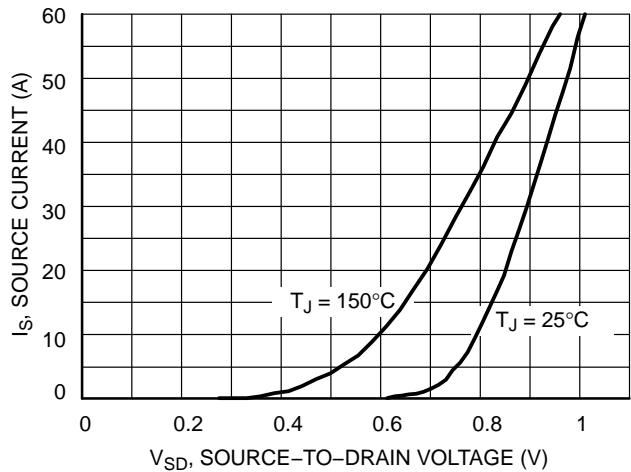


Figure 10. Diode Forward Voltage versus Current

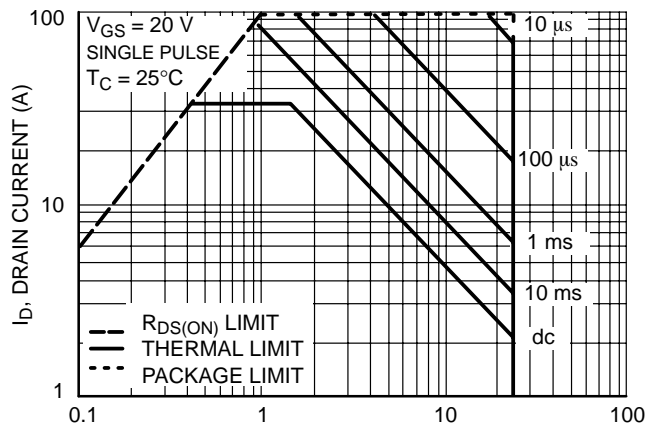
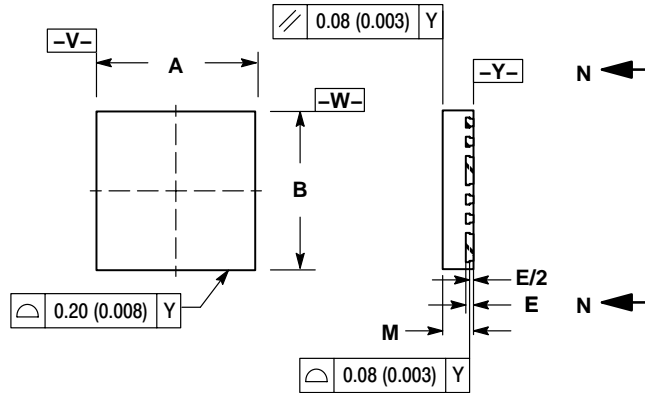


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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PACKAGE DIMENSIONS

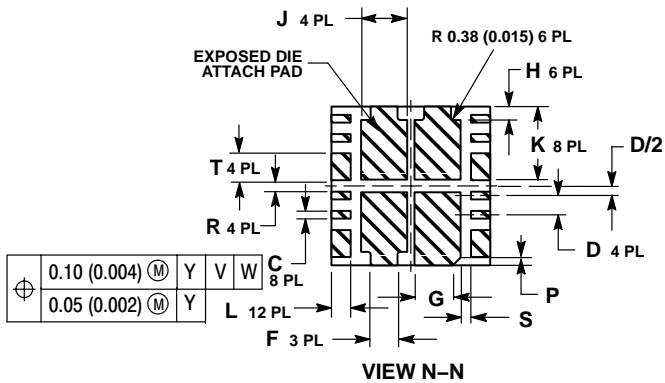
PlnPAK
CASE 495-01
ISSUE O




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. COPLANARITY APPLIES TO LEAD, DIE ATTACHED PAD.
4. OPTIONAL FEATURES ARE FOR REFERENCE ONLY.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	10.40	10.60	0.409	0.417
B	10.40	10.60	0.409	0.417
C	0.40	0.50	0.016	0.020
D	1.27 BSC		0.050 BSC	
E	0.50	0.52	0.020	0.020
F	1.70	1.90	0.067	0.075
G	2.45	2.55	0.096	0.100
H	0.80	1.00	0.031	0.039
J	2.90	3.10	0.114	0.122
K	4.75	4.95	0.187	0.195
L	1.10	1.30	0.043	0.051
M	2.00	2.20	0.079	0.087
P	0.30	0.50	0.012	0.020
R	0.70	0.90	0.028	0.035
S	0.58	0.78	0.023	0.031
T	1.68	1.78	0.066	0.070



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